

2SA1225 TRANSISTOR (PNP)

FEATURES

- High Transition Frequency
- Complementary to 2SC2983

APPLICATIONS

- Power Amplifier Applications
- Driver Stage Amplifier Applications



MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit	
V _{CBO}	Collector-Base Voltage	-160	V	
V _{CEO}	Collector-Emitter Voltage	-160	V	
V _{EBO}	Emitter-Base Voltage	-5	V	
Ic	Collector Current	-1.5	А	
Pc	Collector Power Dissipation	1	W	
Tj	Junction Temperature	150	°C	
T _{stg}	Storage Temperature	-55~150	°C	

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-1mA ,I _E =0	-160			V
Collector-emitter breakdown voltage	V _(BR) CEO*	I _C =-10mA, I _B =0	-160			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-1mA,I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =160V,I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V,I _C =0			-0.1	μA
DC current gain	h _{FE}	V _{CE} =-5V, I _C =-0.1A	70		240	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-0.5A,I _B =-50mA			-1.5	V
Base-emitter voltage	V _{BE}	V _{CE} =-5V, I _C =-0.5A			-1	V
Transition frequency	f _T	V _{CE} =-10V ,I _C =-100mA		100		MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V ,I _E =0,f=1MHz		30		pF

^{*} Pulse test

CLASSIFICATION OF her

Rank	0	Y
Range	70-140	120-240



